

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7	angle near10 acute near10 rhombus near10 ("60" or "120")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:13
L2	110	(grind\$5 or ground\$5) near10 (back or rear) near15 cut\$6 near15 chip	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:13
L3	142	117/915.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:13
L4	560	117/937.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:14
L5	3046	(GaN or Gallium near2 nitride) near15 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:14
L6	103	(GaN or Gallium near2 nitride) near15 electrode same cut\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:14
L7	205	(shiro near2 sakai or yves near2 lacroix).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:15
L8	56	(shiro near2 sakai or yves near2 lacroix).in. and (GaN or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:15
L9	3	(shiro near2 sakai or yves near2 lacroix).in. and (GaN or gallium near2 nitride) and cut\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:15
S1	2	"20020124794".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:13

S2	53	semiconductor near15 rhombus	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 13:29
S3	15	"961328"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 13:33
S4	23	(back or rear) near10 grind\$5 same cleav\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 13:43
S5	1693	(back or rear) near10 grind\$5 same cut\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 13:43
S6	268	(back or rear) near10 grind\$5 same cut\$5 same semiconduct\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 13:44
S7	1	(back or rear) near10 grind\$5 same cut\$5 same semiconduct\$6 same (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 13:45
S8	9	(back or rear) near10 grind\$5 same cut\$5 same semiconduct\$6 and (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 13:45
S9	205	(shiro near2 sakai or yves near2 lacroix).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:06
S10	13	(shiro near2 sakai or yves near2 lacroix).in. and cut\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:07
S11	413	cut\$5 same grind\$5 near10 (back or rear) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:08

S12	4	cut\$5 same grind\$5 near10 (back or rear) same (scratch\$6) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 16:10
S13	110	(grind\$5 or ground\$5) near10 (back or rear) near15 cut\$6 near15 chip	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:13